



## **QS6U24TR Information**



For Reference Only

Part Number QS6U24TR

Manufacturer Rohm Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET P-CH 30V 1A TSMT6

**Package** SOT-23-6 Thin, TSOT-23-6 For the pricing/inventory/lead time, please contact

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Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **QS6U24TR Specifications**

Manufacturer Part NumberQ86U24TRManufacturerRohm SemiconductorCategoryDiscrete Semiconductor Products Transistors - FETs, MOSFETs - SinglePackageSOT-23-6 Thin, TSOT-23-6Series-FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C1A (Ta)Drive Voltage (Max Rds On, Min Rds On)4V, 10VVgs(th) (Max) @ Id2.5V @ ImAGate Charge (Qg) (Max) @ Vgs1.7nC @ 5VInput Capacitance (Ciss) (Max) @ Vds90pF @ 10VVgs (Max)±20VFET FeatureSchottky Diode (Isolated)Power Dissipation (Max)1.25W (Ta)Rds On (Max) @ Id, Vgs400 mOhm @ 1A, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTSMT6 (SC-95)Package / CaseSOT-23-6 Thin, TSOT-23-6	•	
Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  SOT-23-6 Thin, TSOT-23-6  Series  - FET Type  P-Channel  Technology  MOSFET (Metal Oxide)  Jorin to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Schottky Diode (Isolated)  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  400 mOhm @ 1A, 10V  Operating Temperature  Supplier Device Package  TSMT6 (SC-95)  Package / Case  SOT-23-6 Thin, TSOT-23-6	Manufacturer Part Number	QS6U24TR
Package SOT-23-6 Thin, TSOT-23-6 Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C IA (Ta) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgs(th) (Max) @ Id 2.5V @ ImA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 90pF @ 10V Vgs (Max) ±20V FET Feature Schottky Diode (Isolated) Power Dissipation (Max) Rds On (Max) @ Id, Vgs 400 mOhm @ 1A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TSMT6 (SC-95) Package / Case SOT-23-6 Thin, TSOT-23-6	Manufacturer	Rohm Semiconductor
Package SOT-23-6 Thin, TSOT-23-6 Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 1A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgs(th) (Max) @ Id 2.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 1.7nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 90pF @ 10V Vgs (Max) ±20V FET Feature Schottky Diode (Isolated) Power Dissipation (Max) 1.25W (Ta) Rds On (Max) @ Id, Vgs 400 mOhm @ 1A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TSMT6 (SC-95) Package / Case SOT-23-6 Thin, TSOT-23-6	Category	Discrete Semiconductor Products
Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 1A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgs(th) (Max) @ Id 2.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 1.7nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 90pF @ 10V Vgs (Max) ±20V FET Feature Schottky Diode (Isolated) Power Dissipation (Max) 1.25W (Ta) Rds On (Max) @ Id, Vgs 400 mOhm @ 1A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TSMT6 (SC-95) Package / Case SOT-23-6 Thin, TSOT-23-6		Transistors - FETs, MOSFETs - Single
FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 1A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgs(th) (Max) @ Id 2.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 1.7nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 90pF @ 10V Vgs (Max) ±20V FET Feature Schottky Diode (Isolated) Power Dissipation (Max) 1.25W (Ta) Rds On (Max) @ Id, Vgs 400 mOhm @ 1A, 10V Operating Temperature 150°C (TI) Mounting Type Surface Mount Supplier Device Package TSMT6 (SC-95) Package / Case SOT-23-6 Thin, TSOT-23-6	Package	SOT-23-6 Thin, TSOT-23-6
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  1A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  1.7nC @ 5V  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Schottky Diode (Isolated)  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  400 mOhm @ 1A, 10V  Operating Temperature  Supplier Device Package  Package / Case  MOSFET (Metal Oxide)  30V  MOSFET (Metal Oxide)  1A (Ta)  4V, 10V  2.5V @ 1mA  4V, 10V  2.5V @ 1mA  4V, 10V  5Vg (ImA)  1.2FW (InD)  Supplier Device Package  TSMT6 (SC-95)  Package / Case	Series	-
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  1A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Schottky Diode (Isolated)  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  TSMT6 (SC-95)  Package / Case  SOT-23-6 Thin, TSOT-23-6	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Schottky Diode (Isolated)  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  A00 mOhm @ 1A, 10V  Operating Temperature  Supplier Device Package  TSMT6 (SC-95)  Package / Case  SOT-23-6 Thin, TSOT-23-6	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Schottky Diode (Isolated)  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  400 mOhm @ 1A, 10V  Operating Temperature  Supplier Device Package  TSMT6 (SC-95)  Package / Case  SOT-23-6 Thin, TSOT-23-6	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Schottky Diode (Isolated)  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  400 mOhm @ 1A, 10V  Operating Temperature  150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  TSMT6 (SC-95)  Package / Case  SOT-23-6 Thin, TSOT-23-6	Current - Continuous Drain (Id) @ 25°C	1A (Ta)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  90pF @ 10V  Vgs (Max)  ±20V  FET Feature  Schottky Diode (Isolated)  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  400 mOhm @ 1A, 10V  Operating Temperature  150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  TSMT6 (SC-95)  Package / Case	Drive Voltage (Max Rds On, Min Rds On)	4V, 10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Schottky Diode (Isolated)  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  400 mOhm @ 1A, 10V  Operating Temperature  150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  TSMT6 (SC-95)  Package / Case  SOT-23-6 Thin, TSOT-23-6	Vgs(th) (Max) @ Id	2.5V @ 1mA
Vgs (Max)±20VFET FeatureSchottky Diode (Isolated)Power Dissipation (Max)1.25W (Ta)Rds On (Max) @ Id, Vgs400 mOhm @ 1A, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTSMT6 (SC-95)Package / CaseSOT-23-6 Thin, TSOT-23-6	Gate Charge (Qg) (Max) @ Vgs	1.7nC @ 5V
FET Feature Schottky Diode (Isolated) Power Dissipation (Max) Rds On (Max) @ Id, Vgs 400 mOhm @ 1A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TSMT6 (SC-95) Package / Case SOT-23-6 Thin, TSOT-23-6	Input Capacitance (Ciss) (Max) @ Vds	90pF @ 10V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  400 mOhm @ 1A, 10V  Operating Temperature  150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  TSMT6 (SC-95)  Package / Case  SOT-23-6 Thin, TSOT-23-6	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs400 mOhm @ 1A, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTSMT6 (SC-95)Package / CaseSOT-23-6 Thin, TSOT-23-6	FET Feature	Schottky Diode (Isolated)
Operating Temperature 150°C (TJ)  Mounting Type Surface Mount  Supplier Device Package TSMT6 (SC-95)  Package / Case SOT-23-6 Thin, TSOT-23-6	Power Dissipation (Max)	1.25W (Ta)
Mounting Type Surface Mount Supplier Device Package TSMT6 (SC-95) Package / Case SOT-23-6 Thin, TSOT-23-6	Rds On (Max) @ Id, Vgs	400 mOhm @ 1A, 10V
Supplier Device Package TSMT6 (SC-95) Package / Case SOT-23-6 Thin, TSOT-23-6	Operating Temperature	
Package / Case SOT-23-6 Thin, TSOT-23-6	Mounting Type	Surface Mount
	Supplier Device Package	TSMT6 (SC-95)
Report errors?	Package / Case	SOT-23-6 Thin, TSOT-23-6
Report circles:		Report errors?

## **QS6U24TR Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **QS6U24TR Payment Methods**



















### **QS6U24TR Shipping Methods**













If you have any question about QS6U24TR, please do not hesitate to contact us!

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